

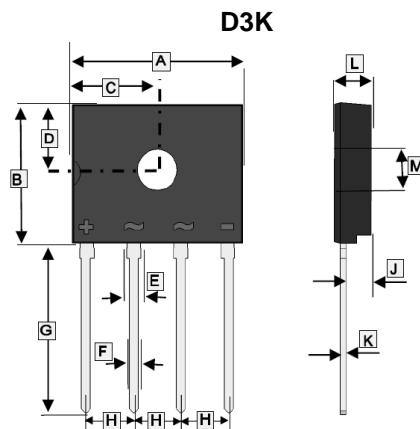
2.0Amp Glass Passivated Bridge Rectifiers

FEATURES

- $I_o : 2A$
- $V_{RRM} : 50\sim1000V$
- Glass passivated chip
- High surge forward current capability

APPLICATIONS

- General purpose 1 phase Bridge rectifier applications



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	13.3	14.3	G	13.1	13.5
B	10.3	11.3	H	3.7	3.9
C	6.4	7.4	J	2.0	2.2
D	4.5	5.5	K	0.4	0.6
E	1.05	1.45	L	2.6	3.6
F	0.60	0.85	M	3.1	3.4

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Rating 25°C ambient temperature unless otherwise specified. Single phase half wave, 60Hz, resistive or inductive load.
For capacitive load, de-rate current by 20%.)

Parameter	Symbol	T2BU							Unit
		01	02	03	04	06	08	10	
Maximum repetitive peak reverse voltage	Vrrm	50	100	200	400	600	800	1000	V
Maximum RMS voltage	Vrms	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	Vdc	50	100	200	400	600	800	1000	V
Maximum average forward rectified output current Tc 143°C with heatsink	If(av)					2.0			A
Peak forward surge current single sine-wave superimposed on rated load (JEDEC Method)	Ifsm					62			A
Maximum instantaneous forward voltage drop per leg at 2.0A	Vf				1.05				V
Rating for fusing (3ms ≤ t < 8.3ms)	I ² t				16				A ² Sec
Maximum DC reverse current at rated DC blocking voltage per leg	Ir				500				μA
Thermal resistance	without heatsink with heatsink without heatsink	Rth(ja) Rth(jc) Rth(jl)			55 1.5 15				°C/W
Operating junction and storage temperature range	Tj, Tstg				-55 to +150				°C

RATINGS AND CHARACTERISTIC CURVES T2BU01 THRU T2BU10

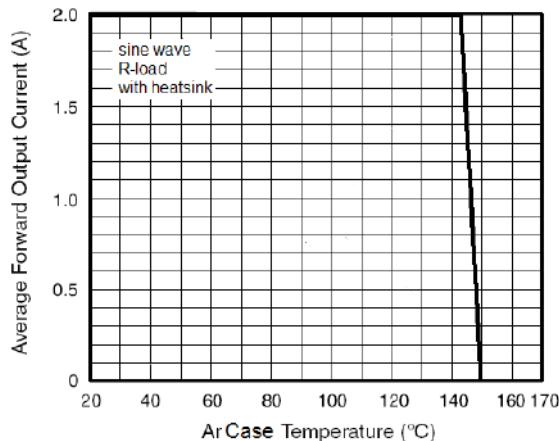


Figure 1. Derating Curve Output Rectified Current

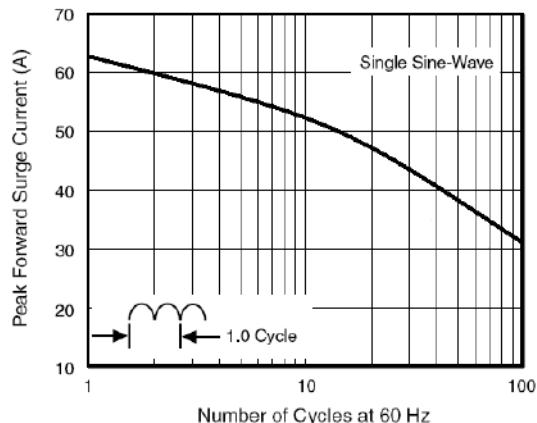


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

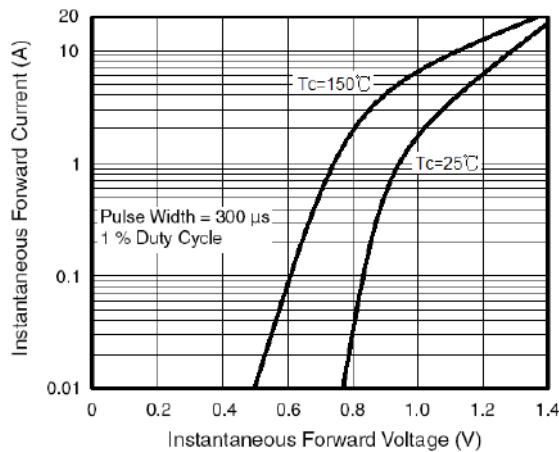


Figure 3. Typical Forward Characteristics Per Diode

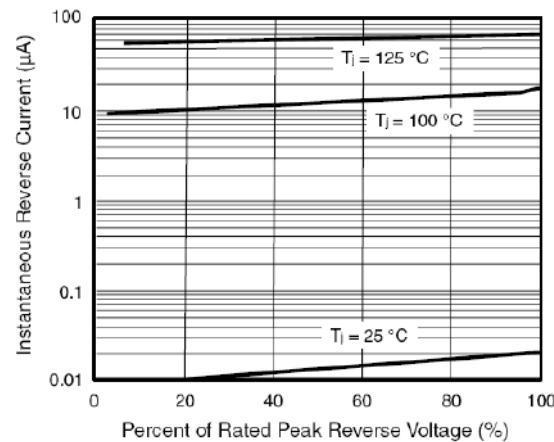


Figure 4. Typical Reverse Leakage Characteristics Per Diode

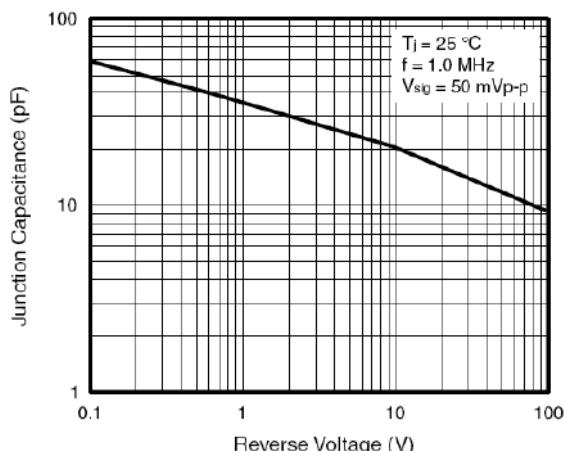


Figure 5. Typical Junction Capacitance Per Diode